SILICON PNP MEDIUM POWER TRANSISTOR

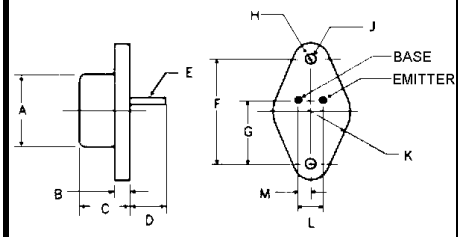
DESCRIPTION:

The **2N3740** is a Medium Power Transistor for General Purpose Amplifier and Switching Applications.

MAXIMUM RATINGS

I_C	4.0 A
V_{CEO}	-60 V
P_{DISS}	25 W @ T_C = 25 °C
T_J	-65 to +200 °C
T_{STG}	-65 to +200 °C
θ_{JC}	7 °C/W

PACKAGE STYLE TO- 66



	INCHES	MILLIMETERS
A	.620 MAX.	15.75 MAX.
B	.050 - .075	1.27 - 1.90
C	.250 - .340	6.35 - 8.63
D	.360 MIN.	9.14 MIN.
E	.028 - .034 DIA.	.711 - .863
F	.958 - .962	24.33 - 24.43
G	.570 - .590	14.47 - 14.98
H	.145 MAX. RAD.	3.68 MAX. RAD.
J	.142 - .152 DIA.	3.60 - 3.86 DIA.
K	.350 MAX. RAD.	8.89 MAX. RAD.
L	.190 - .210	4.82 - 5.33
M	.093 - .107	2.36 - 2.72

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I_C = 100 mA	-60			V
I_{CEX}	V_{CE} = -60 V V_{BE} = 1.5 V T_C = 150 °C			0.1 1	mA
I_{CB0}	V_{CE} = -60 V			100	µA
I_{CEO}	V_{CE} = -40 V			1.0	mA
I_{EBO}	V_{EB} = -7.0 V			500	nA
h_{FE}	V_{CE} = -1.0 V I_C = 100 mA I_C = 250 mA I_C = 500 mA I_C = 1.0 A	40 30 20 10		100	---
$V_{CE(SAT)}$	I_C = 1.0 A I_B = 125 mA			-0.6	V
$V_{BE(ON)}$	V_{CE} = -1.0 V I_C = 1.0 A			-1.0	V
h_{fe}	V_{CE} = -10 V I_C = 50 mA f = 1.0 KHz	25			---
f_T	V_{CE} = -10 V I_C = 100 mA f = 1.0 MHz	3.0			MHz
C_{OB}	V_{CB} = -10 V f = 100 KHz			100	pF